Study of Quasi-Z-Source Cascaded H-Bridge Multilevel Inverter with Voltage-Lift Cell

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Abstract

Background/Objectives: Quasi-Z-source based multilevel inverters have attracted much interest in recent research works due to its valuable merits when evaluated with conventional voltage source inverters and Z-source Inverters. The objectives of this research work is to provide lower power rating of power devices, continuous input current, higher boosted output voltage and reduced current stress for dc source.

Methods/Statistical analysis: A new quasi-Z-source Cascaded H-Bridge multilevel inverter with voltage-lift cell (VL-qZS-CHB-MLI) is analysed in this research paper. The performance of the VL-qZS-CHB-MLI is verified through simulation results obtained using multicarrier PD-PWM technique with simple boost control strategy. Shoot-through states are introduced in generated pulses by utilizing the simple boost control technique. Extended boost operation of the proposed topology is provided by the shoot-through states.

Findings: In this new proposed topology, the presence of voltage-lift cell significantly strengthens the boost capability for the equal shoot-through duty ratio as in traditional qZS-CHB-MLI. The proposed topology involves lower shoot-through duty ratio as in the qZS-CHB-MLI for achieving the same boost gain. This advantage of the proposed topology makes possible the larger improvement in the output voltage.

Application/Improvements: The proposed topology can be popularly utilized for high-power applications requiring good quality boosted output and low voltage stress. Also, the proposed topology offered abundant merits over traditional Cascaded H-Bridge (CHB) multilevel inverter in distributed power generation applications like PV power system and wind energy system.

Keywords: Cascaded H-Bridge (CHB) Multilevel Inverter, PD-PWM, Quasi-Z-Source, Simple Boost Control, Voltage-Lift Cell

1. Introduction

The Z-source based multilevel inverters created a centre of attention in modern research works owing to its fruitful advantages in contrast with conventional voltage source inverters and Z-source inverters (ZSI). The ZSI has a one-stage power conversion capability that makes use of shoot-through and non-shoot-through states to provide boosted output voltage, thus achieving high immunity to the Electro-Magnetic

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Interference (EMI) noise\textsuperscript{4-5}. However, it has noticeable flaws including high voltage stress across the capacitors and switching devices, high incoming current and lower boosting capability. The major negative aspect of the ZSI is the irregular input current that may lead to rude operation and permanent failure of the dc source. To overcome the flaws associated with the ZSI, various improved circuit structures\textsuperscript{6-11} were presented in the literature.

A new extended-boost ZSI\textsuperscript{6} is presented with a capacitor/diode, which provides increased boost factor and continuous current, but it has complex circuit structure. The quasi-Z-Source Inverter (qZSI): portrays the advantages of lower number of power devices with lower power rating. Also, in recent days multilevel inverters are popularly utilized for high-power applications with good quality output and low voltage stress\textsuperscript{12}. CHB multilevel inverter has more advantages over Diode clamped and Capacitor clamped multilevel inverters for a given number of levels\textsuperscript{13-15}. The qZSI concept has been applied to CHB multilevel inverter, providing combined advantages of CHB multilevel inverter and qZSI\textsuperscript{12}. The quasi-Z-Source Cascaded H-Bridge Multi-Level Inverter (qZS-CHB-MLI) offered abundant merits over traditional CHB multilevel inverter in distributed generation applications. A new Voltage-Lift quasi-Z-Source Cascaded H-Bridge Multilevel Inverter (VL-qZS-CHB-MLI) is presented in this paper to further increase the boosting capability. The new VL-qZS-CHB-MLI provides extended boosting capability for the equal shoot-through duty ratio as in the qZS-CHB-MLI.

The traditional qZS-CHB-MLI is explained in section II with circuit topology and characteristics of boost factor and shoot-through duty ratio. The VL-qZS-CHB-MLI is explained in section III. The PWM control strategy of the proposed VL-qZS-CHB-MLI is given in section IV. The simulation results of the VL-qZS-CHB-MLI are portrayed in section V. Lastly, the conclusion is specified in section VI.

### 2. Traditional qZS-CHB-MLI

Figure 1. shows the traditional qZS-CHB-MLI, which comprises a qZ-source-network with two inductors (L\textsubscript{1}, L\textsubscript{2}), two capacitors (C\textsubscript{1}, C\textsubscript{2}) and one diode (D\textsubscript{1}).

In this traditional topology, qZ source network shares the common ground with inverter. The boost factor (B) of the qZS-CHB-MLI is given in (1)

\[
B = \frac{V_{dc}}{V_{in}} = \frac{1}{1 - 2D_{sh}}
\]

### 3. Proposed VL-qZS-CHB-MLI

To enhance the boost ability of the traditional qZS-CHB-MLI, a voltage-lift cell is incorporated by replacing inductor L\textsubscript{2} in that topology to form a new proposed topology VL-qZS-CHB-MLI which is shown in Figure 2.

#### 3.1 Shoot-Through Control State

In shoot-through control state depicted in Figure 3, the inductors L\textsubscript{2}, L\textsubscript{3} and capacitor C\textsubscript{3} are in shunt connection, where the diodes D\textsubscript{2} and D\textsubscript{3} are on and D\textsubscript{1} is off. The capacitor C\textsubscript{3} is charged, while C\textsubscript{2} and C\textsubscript{1} are discharged.
All the inductors $L_1$, $L_2$ and $L_3$ store energy during this state. Thus, we can state the inductor voltages ($V_{L1}$, $V_{L2}$, $V_{L3}$) and capacitor voltages ($V_{C1}$, $V_{C2}$, $V_{C3}$) as given below in (2).

$$\begin{align*}
V_{L1} &= V_{in} + V_{C2} \\
V_{L2} &= V_{L3} = V_{C1} = V_{C3}
\end{align*}$$

(2)

3.2 Non-Shoot-Through Control State

In non-shoot-through control state depicted in Figure 4, the inductors $L_3$, $L_2$ and $C_3$ are in series connection, where diodes $D_2$ and $D_3$ are off and $D_1$ is on. The capacitor $C_3$ is discharged, while $C_1$ and $C_2$ are charged. All inductors $L_3$, $L_2$ and $L_1$ transmit energy from dc source to load. Thus, we can obtain the inductor voltages and capacitor voltages as given in (3).

$$\begin{align*}
V_{C1} &= V_{in} + V_{L1} \\
V_{C2} &= V_{C3} + V_{L2} + V_{L3} \\
V_{dc} &= V_{C1} + V_{C2}
\end{align*}$$

(3)

Figure 4. Equivalent circuit of the proposed VL-qZS-CHB-MLI under non-shoot-through.

Figure 5 depicts the boosting capability of the VL-qZS-CHB-MLI, which is considerably superior when evaluated with traditional topology. Total harmonic
distortion is high for lower modulation index which results in significant degrade in the ac output voltage. In the most favourable design of the quasi-Z-source multi-level inverter, the value of the modulation index is chosen near to 1. Consequently, the boost factor of quasi-Z-source impedance network is limited by shoot-through duty ratio and modulation index. Simple boost control method is adopted for the proposed topology, which is well known for its easy implementation and reduced current stress across the components. Fig.6 illustrates the characteristics of voltage gain and the modulation index for the VL-qZS-CHB-MLI topology, and it is observed from the plot that the voltage gain rises as the modulation index reduces. Therefore, the proposed topology utilizes higher modulation index for the identical voltage conversion ratio when compared to convention qZS-MLI.

![Figure 6. Voltage conversion ratios of the traditional and proposed topology.](image)

4. PWM Control Strategy of the Proposed VL-qZS-CHB-MLI

The switching signals for the proposed topology are produced by Phase Disposition Pulse Width Modulation (PD-PWM) method. In PD-PWM, the triangular carriers are in phase with each other, having identical frequency \( f_c \) and identical amplitude \( A_c \). In this technique, the reference signal with an amplitude \( A_m \) and frequency \( f_m \) is compared with each of the triangular carrier signals to create gate pulses. Shoot-through states can be generated by simple boost control, maximum boost control and constant boost control methods. For the VL-qZS-CHB-MLI, the shoot-through states are introduced in the generated pulses with PD-PWM technique utilizing simple boost control method. The shoot-through states provide extended boost operation of the proposed topology. The simple boost control strategy employs a constant line with amplitude identical to or larger than the crest value of the modulating signal to produce the shoot-through states.

For this case, the shoot-through duty ratio is given in (4).

\[
D_{zh} = \frac{T_{zh}}{T} = 1 - M
\]

Where, the correlation between modulation index \( M \) and shoot-through duty ratio is given in (5).

\[
M < 1 - D_{zh}
\]

The boost factor of VL-qZS-CHB-MLI is shown in (6).

\[
\beta = \frac{2}{1 - 3D_{zh}}
\]

The proposed topology involves lower shoot-through duty ratio when compared with qZS-CHB-MLI for attaining the same boost gain. This improvement of the VL-qZS-CHB-MLI topology makes possible the larger improvement in the output voltage.

5. Simulation Results

To address the virtues of the VL-qZS-CHB-MLI topology shown in Figure 2, the simulation results obtained through Matlab is compared with that of the traditional topology. Figure 7 and 8 illustrate the simulation results of the VL-qZS-CHB-MLI and their simulation parameter are provided in Table 1.

<table>
<thead>
<tr>
<th>Input DC Voltage</th>
<th>( V_{in} )</th>
<th>100V</th>
</tr>
</thead>
<tbody>
<tr>
<td>VL-qZS network</td>
<td>( L = L_1 = L_2 = L_3 )</td>
<td>40 mH</td>
</tr>
<tr>
<td></td>
<td>( C = C_1 = C_2 = C_3 )</td>
<td>6000 ( \mu F )</td>
</tr>
<tr>
<td>Switching frequency</td>
<td>( f_s )</td>
<td>10 KHz</td>
</tr>
<tr>
<td>Resistive Load</td>
<td>( R )</td>
<td>50Ω</td>
</tr>
</tbody>
</table>

As exposed in Figure 9, in steady state, \( V_{dc} \) is increased to 300V for the given dc voltage of 100V. The capacitor voltages \( V_{c1} \) & \( V_{c2} \) for the proposed topology are boosted...
to 160V and 140V approximately, which are same with analysis and shown in Figure 8.

Figure 7. Simulation results of the dc link voltages: (a) \( V_{dc1} \), (b) \( V_{dc2} \), (c) \( V_{dc3} \).

Figure 8. Capacitor voltages (\( V_{C1} \) & \( V_{C2} \)) of the proposed topology

6. Conclusion

A new voltage-lift quasi-Z-Source Cascaded MLI with higher boost ability is compared with traditional quasi-Z-source Cascaded MLI. The higher boost ability of the proposed topology improves the quality of the output voltage waveform. The study of the new proposed topology is verified by simulation results obtained with simple boost control method. This topology is appropriate for distributed power generation applications such as PV power system and wind energy system.

7. References